ALPHA & OMEGA
SEMICONDUCTOR, LTD

AO6806
Dual N-Channel Enhancement Mode Field Effect Transistor

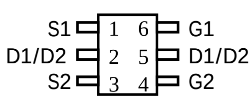
General Description

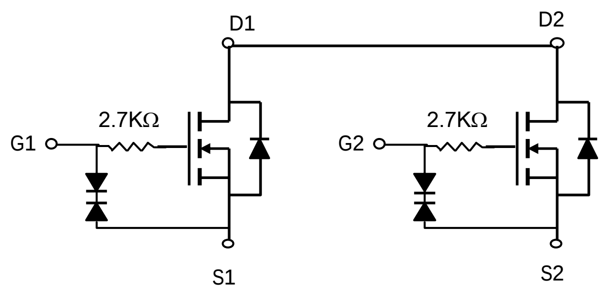
The AO6806 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications. *AO6806 is Pb-free (meets ROHS & Sony 259 specifications).*

Features

V_{DS} = 20V
I_D = 5.0A (${V_{GS}}$ = 4.5V)
$R_{DS(ON)}$ < 33mΩ (V_{GS} = 4.5V)
$R_{DS(ON)}$ < 34mΩ (V_{GS} = 4.0V)
$R_{DS(ON)}$ < 36mΩ (V_{GS} = 3.1V)
$R_{DS(ON)}$ < 40mΩ (V_{GS} = 2.5V)

TSOP6
Top View





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	10 Sec	Steady State	Units
Drain-Source Voltage		V_{DS}	20		V
Gate-Source Voltage		V_{GS}	±12		V
Continuous Drain Current [A]	T_A=25°C	I_D	5	3.8	A
	T_A=70°C		3.8	3	
Pulsed Drain Current [B]		I_{DM}	25		
Power Dissipation [A]	T_A=25°C	P_D	1.3	0.8	W
	T_A=70°C		0.8	0.5	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150		°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	76	95	°C/W
Maximum Junction-to-Ambient [A]	Steady State		118	150	°C/W
Maximum Junction-to-Lead [C]	Steady State	$R_{\theta JL}$	54	68	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
STATIC PARAMETERS							
BV_{DSS}	Drain-Source Breakdown Voltage	I_D = 250µA, V_{GS} = 0V		20			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 20V, V_{GS} = 0V				1	µA
			T_J = 55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS} = 0V, V_{GS} = ±10V				±10	µA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS} I_D = 250µA		0.5	0.7	1	V
$I_{D(ON)}$	On state drain current	V_{GS} = 4.5V, V_{DS} = 5V		25			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS} = 4.5V, I_D = 5.0A		21	27	33	mΩ
			T_J=125°C	29	37	45	
		V_{GS} = 4.0V, I_D = 4.5A		22	28	34	mΩ
		V_{GS} = 3.1V, I_D = 4.5A		24	30	36	mΩ
		V_{GS} = 2.5V, I_D = 4.0A		26	33	40	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 5V, I_D = 5.0A			18		S
V_{SD}	Diode Forward Voltage	I_S = 1A,V_{GS} = 0V			0.65	1	V
I_S	Maximum Body-Diode Continuous Current					1.3	A
DYNAMIC PARAMETERS							
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=10V, f=1MHz			180	225	pF
C_{oss}	Output Capacitance				95		pF
C_{rss}	Reverse Transfer Capacitance				18		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz			2.7	4	kΩ
SWITCHING PARAMETERS							
Q_g (4.5V)	Total Gate Charge	V_{GS}= 4.5V, V_{DS}= 10V, I_D= 5A			5.6	7.5	nC
Q_{gs}	Gate Source Charge				0.85		nC
Q_{gd}	Gate Drain Charge				1.7		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=10V, R_L=2.0Ω, R_{GEN}=3Ω			172		ns
t_r	Turn-On Rise Time				368		ns
$t_{D(off)}$	Turn-Off DelayTime				2.94		µs
t_f	Turn-Off Fall Time				2.5		µs
t_{rr}	Body Diode Reverse Recovery Time	I_F=5A, dI/dt=100A/µs			32	43	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=5A, dI/dt=100A/µs			3.2		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in ^{2} FR-4 board with 2oz. Copper, in a still air environment with T_A = 25°C. in any given application depends on the user's specific board design. The current rating is based on the t ≤10s thermal resistance rating.
B: Repetitive rating, pulse width limited by junction temperature.
C. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.
D. The static characteristics in Figures 1 to 6 are obtained using < 300 µs pulses, duty cycle 0.5% max.
E. These tests are performed with the device mounted on 1 in ^{2} FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

Rev0: Nov 2007

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

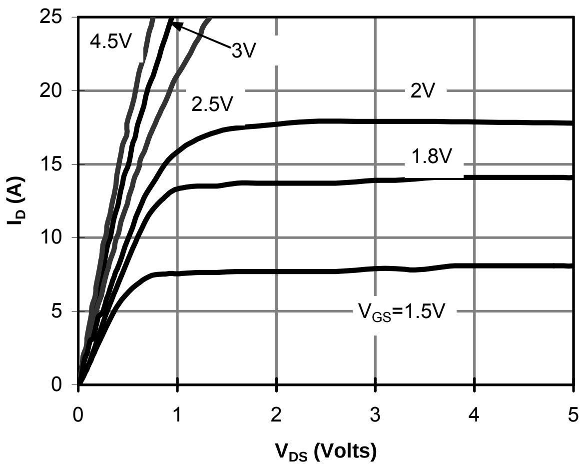


Figure 1: On-Region Characteristics

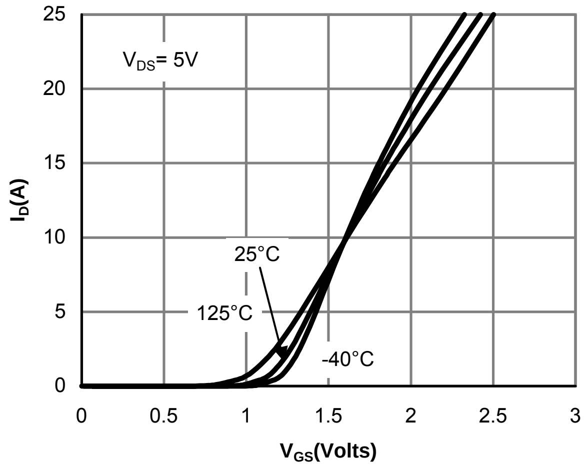


Figure 2: Transfer Characteristics

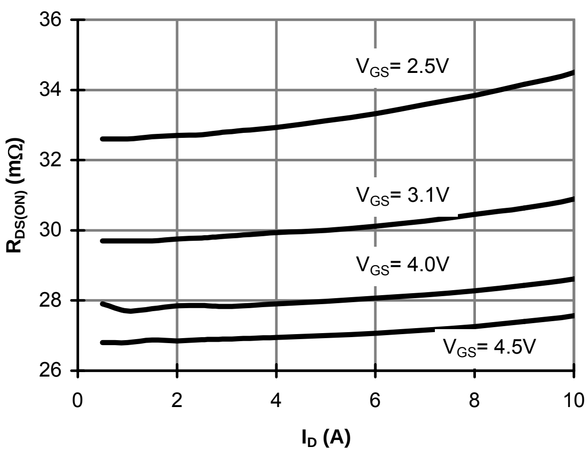


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

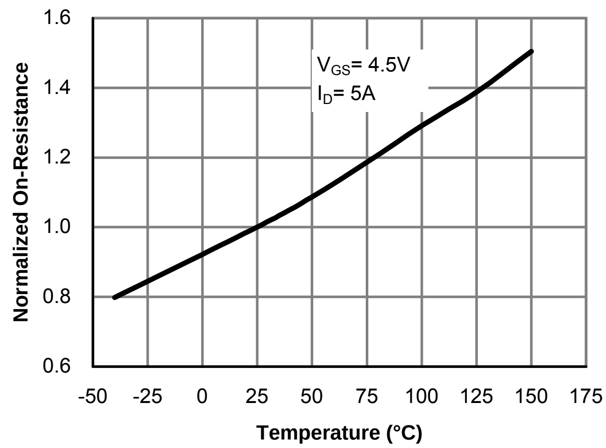


Figure 4: On-Resistance vs. Junction Temperature

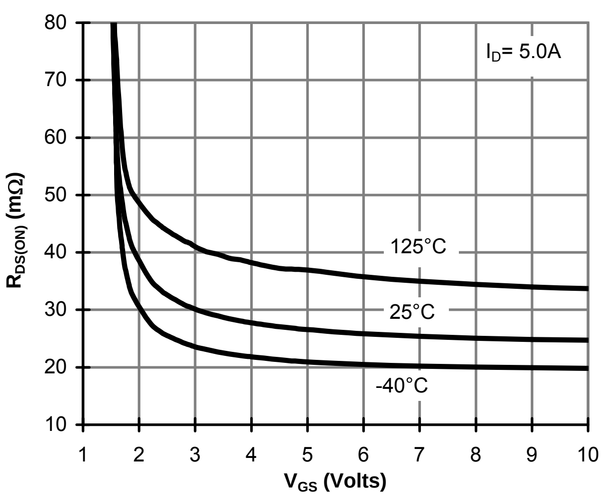


Figure 5: On-Resistance vs. Gate-Source Voltage

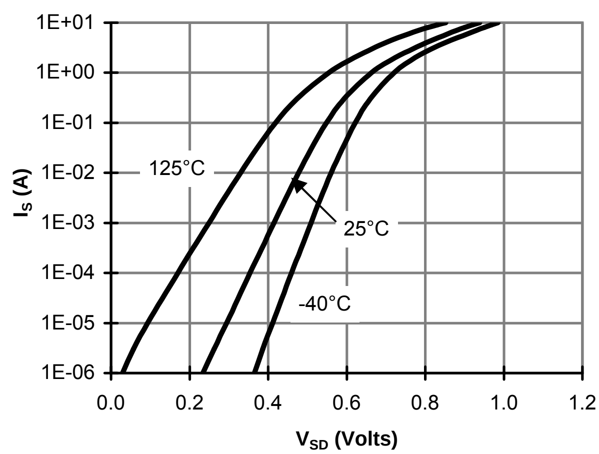


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

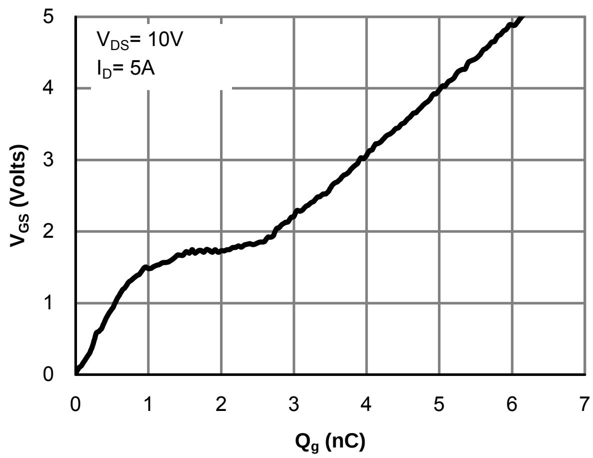


Figure 7: Gate-Charge Characteristics

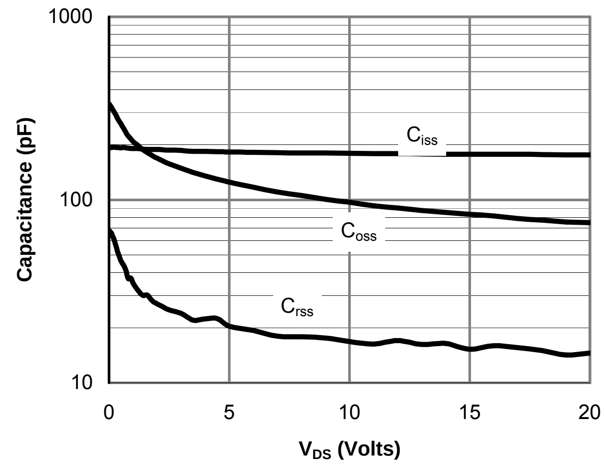


Figure 8: Capacitance Characteristics

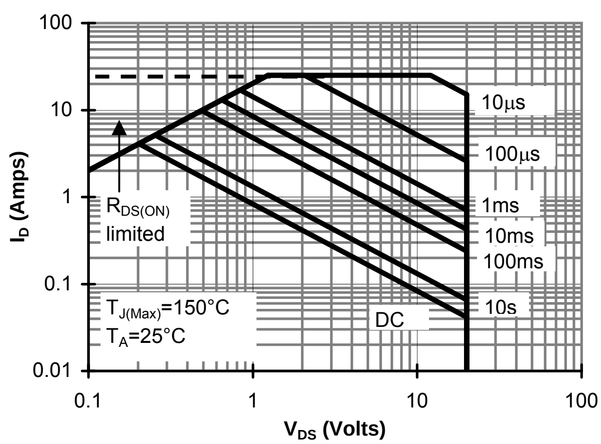


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

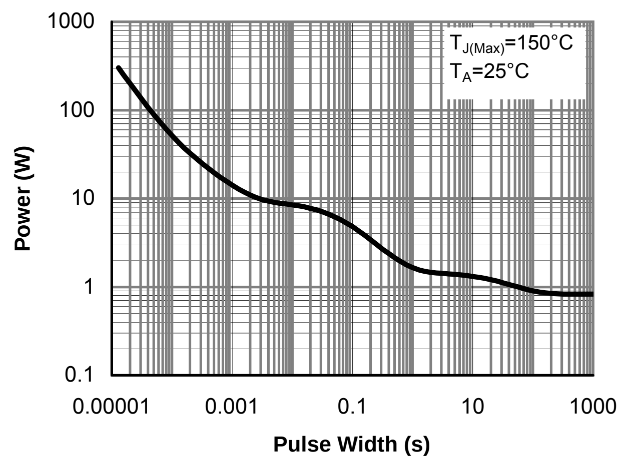


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

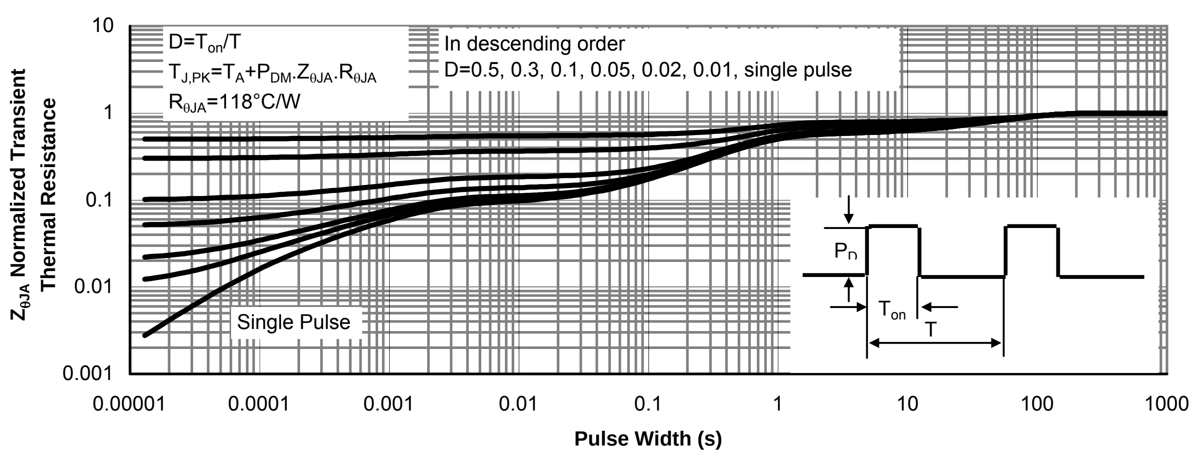


Figure 11: Normalized Maximum Transient Thermal Impedance(Note E)